



Vishay Siliconix

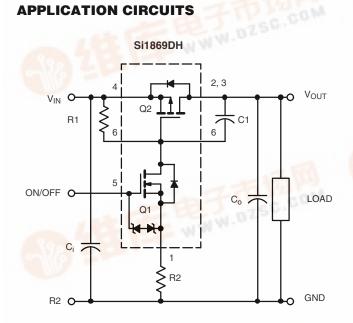
Load Switch with Level-Shift

PRODUCT SUMMARY			
V _{DS2} (V)	R_{DS(on)} (Ω)	I _D (A)	
1.8 to 20	0.165 at V _{IN} = 4.5 V	± 1.2	
	0.222 at V _{IN} = 2.5 V	± 1.0	
	0.303 at V _{IN} = 1.8 V	± 0.7	

DESCRIPTION

The Si1869DH includes a p- and n-channel MOSFET in a single SC70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a levelshift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1869DH operates on supply lines from 1.8 V to 20 V, and can drive loads up to 1.2 A.

APPLICATION CIRCUITS

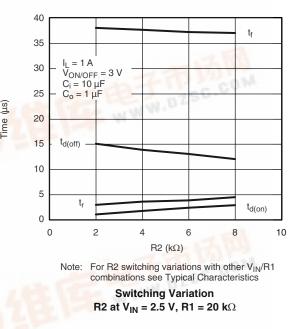


FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs: 1.8 V Rated
- ESD Protected: 2000 V On Input Switch,
- VON/OFF
- 165 mΩ Low R_{DS(on)}
- 1.8 to 20 V Input
- 1.5 to 8 V Logic Level Control
- Low Profile, Small Footprint SC70-6 Package
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Level Shift for Portable Devices



The Si1869DH is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

COMPONENTS					
R1	Pull-Up Resistor	Typical 10 k Ω to 1 M Ω^*			
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω^*			
C1	Optional Slew-Rate Control	Typical 1000 pF			

* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

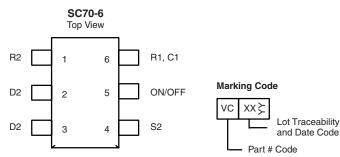


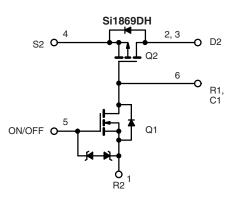
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FUNCTIONAL BLOCK DIAGRAM





Ordering Information: Si1869DH-T1-E3 (Lead (Pb)-free) Si1869DH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage (D2-S2)		V _{DS}	- 20	v		
Input Voltage		V _{IN}	20			
ON/OFF Voltage		V _{ON/OFF}	8			
Load Current	Continuous ^{a, b}	- I <u>L</u>	± 1.2	А		
Load Current	Pulsed ^{b, c}		± 3			
Continuous Intrinsic Diode Conduction ^a		۱ _S	- 0.4			
Maximum Power Dissipation ^a		P _D	1.0	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)		ESD	2	kV		

THERMAL RESISTANCE RATINGS					
Parameter		Typical	Maximum	Unit	
Maximum Junction-to-Ambient (Continuous Current) ^a	R _{thJA}	100	125	°C/W	
Maximum Junction-to-Foot (Q2)	R _{thJF}	44	55	0/10	

SPECIFICATIONS T _J = 25 °C unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
OFF Characteristics						
Reverse Leakage Current	I _{FL}	V _{IN} = 8 V, V _{ON/OFF} = 0 V			1	μA
Diode Forward Voltage	V_{SD}	I _S = - 0.4 A	0.4	0.6	1.1	V
ON Characteristics						
Input Voltage Range	V _{IN}		1.8		20	v
Drain to Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 20			
On-Resistance (P-Channel) at 1 A	R _{DS(on)}	$V_{ON/OFF}$ = 1.5 V, V_{IN} = 4.5 V, I_D = 1.2 A		0.132	0.165	Ω
		$V_{ON/OFF}$ = 1.5 V, V_{IN} = 2.5 V, I_D = 1.0 A		0.177	0.222	
		$V_{ON/OFF}$ = 1.5 V, V_{IN} = 1.8 V, I_D = 0.7 A		0.242	0.303	
On-State (P-Channel) Drain-Current	I _{D(on)}	$V_{\text{IN-OUT}} \leq 0.2$ V, V_{IN} = 5 V, $V_{\text{ON/OFF}}$ = 1.5 V	1			- A
		$V_{\text{IN-OUT}} \leq 0.3$ V, V_{IN} = 3 V, $V_{\text{ON/OFF}}$ = 1.5 V	1			

Notes:

a. Surface mounted on FR4 board.

b. V_{IN} = 20 V, V_{ON/OFF} = 8 V, T_A = 25 °C. c. Pulse test: pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

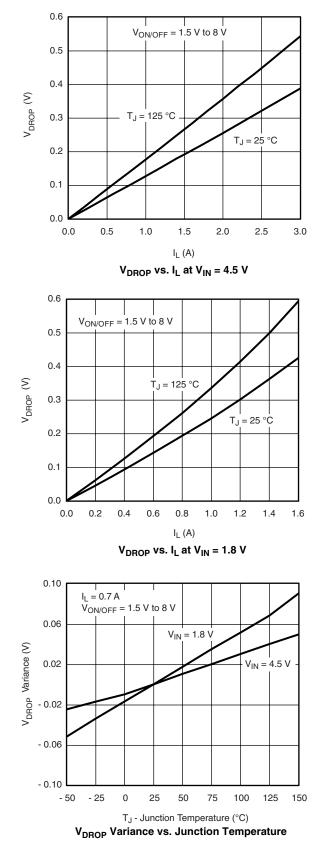
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

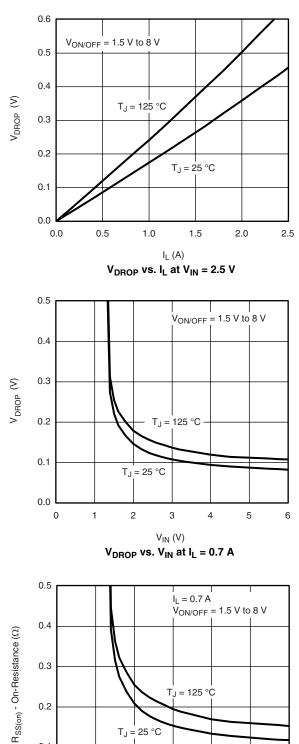


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





T_J = 25 °C

2

3

 $V_{IN}(V)$

On-Resistance vs. Input Voltage

4

0.1

0.0

0

1

5

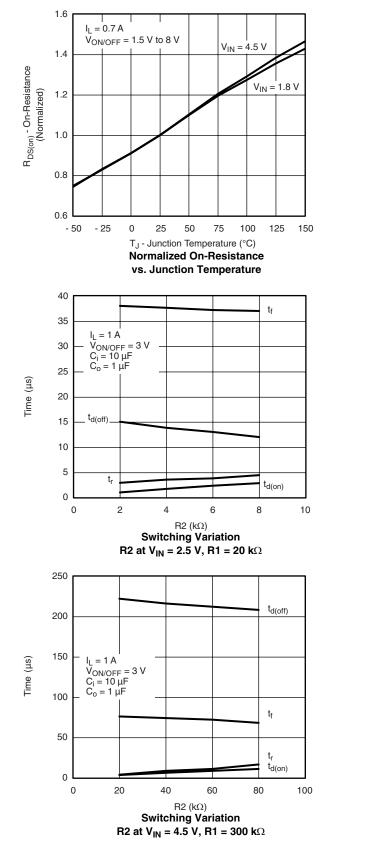
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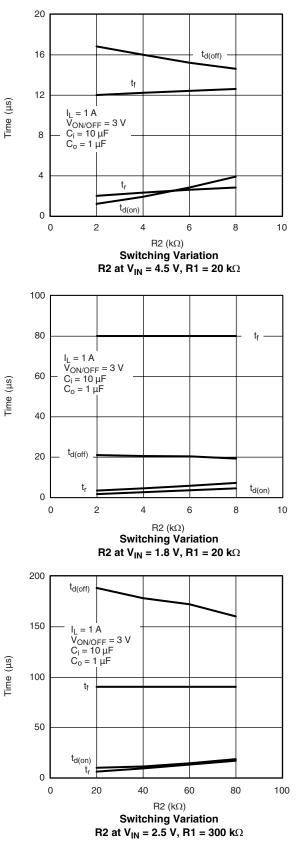
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

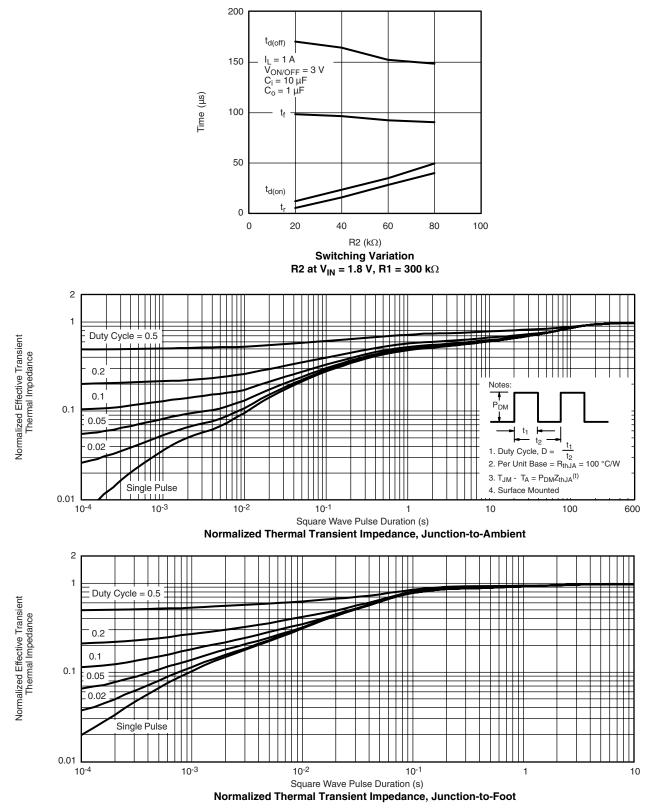






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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73449.



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